

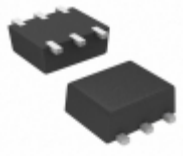


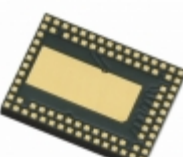
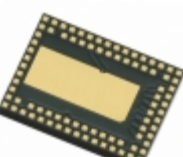
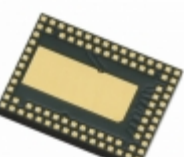

	<p>SI1023CX-T1-GE3</p>
	<p>Hersteller-Teilenummer: SI1023CX-T1-GE3</p> <p>Hersteller / Marke: Electro-Films (EFI) / Vishay</p> <p>Teil der Beschreibung: MOSFET 2P-CH 20V SC89-6</p> <p>Datenblätter:  SI1023CX-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 35896 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI1023CX-T1-GE3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET 2P-CH 20V SC89-6
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	35896 pcs Stock
detaillierte Beschreibung	Mosfet Array 2 P-Channel (Dual) 20V 220mW Surface
Serie	TrenchFET®
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Leistung - max	220mW
Verpackung / Gehäuse	SOT-563, SOT-666
Supplier Device-Gehäuse	SC-89-6
Typ FET	2 P-Channel (Dual)
FET-Merkmal	Logic Level Gate
Drain-Source-Spannung (Vdss)	20V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	-
Rds On (Max) @ Id, Vgs	756 mOhm @ 350mA, 4.5V
VGS (th) (Max) @ Id	1V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	2.5nC @ 4.5V
Eingabekapazität (Ciss) (Max) @ Vds	45pF @ 10V
Verpackung	Tape & Reel (TR)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	SI1023CX-T1-GE3-ND

SI1023CX-T1-GE3 ist neu im Original, Suche SI1023CX-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI1023CX-T1-GE3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SI1023CX-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI1023X-T1-E3 Electro-Films (EFI) / Vishay MOSFET 2P-CH 20V 0.37A SOT563F</p>	 <p>SI1023CX-T1-GE3 Vishay / Siliconix MOSFET 2P-CH 20V SC89-6</p>	 <p>SI1023X-T1-E3 Vishay / Siliconix MOSFET 2P-CH 20V 0.37A SOT563F</p>	 <p>SI1023X-T1 VISHAY SI1023X-T1 VISHAY</p>
 <p>SI1023-B-GMR Energy Micro (Silicon Labs) IC RF TXRX+MCU ISM<1GHZ 85-VFLGA</p>	 <p>SI1023-B-GM Energy Micro (Silicon Labs) IC RF TXRX+MCU ISM<1GHZ 85-VFLGA</p>	 <p>SI1023-B-GM3 Energy Micro (Silicon Labs) IC RF TXRX+MCU ISM<1GHZ 85-VFLGA</p>	 <p>SI1023X VISHAY SI1023X VISHAY</p>

heiße Teile

Mehr

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|------------------|------------------|------------------|-------------------|-------------------|
| ⊛ SI1013R-T1-E3 | ↔ SI1013R-T1-GE3 | ➔ SI1013R-T1-GE3 | D SI1013X-T1 | ➔ SI1013X-T1-E3 |
| ⊣ SI1013X-T1-E3 | ⊛ SI1013X-T1-GE3 | D SI1013X-T1-GE3 | ➔ SI1016CX-T1-GE3 | ➔ SI1016CX-T1-GE3 |
| ⊛ SI1016X-T1-E3 | ⊣ SI1016X-T1-E3 | ⊛ SI1016X-T1-GE3 | ↔ SI1016X-T1-GE3 | ➔ SI1016X2-T1-GE3 |
| D SI1021R-T1 | ⊛ SI1021R-T1-E3 | ⊣ SI1021R-T1-E3 | ⊛ SI1022R-T1 | ➔ SI1022R-T1-E3 |
| ➔ SI1022R-T1-E3 | ↔ SI1022R-T1-GE3 | ⊛ SI1022R-T1-GE3 | ⊣ SI1022R-T1-E3 | ➔ SI1023CX-T1-GE3 |
| ↔ SI1023X-T1 | ➔ SI1023X-T1-E3 | D SI1023X-T1-E3 | ⊛ SI1023X-T1-GE3 | ⊣ SI1023X-T1-GE3 |
| ⊛ SI1024-T1 | D SI1024X-T1 | ➔ SI1024X-T1-E3 | ↔ SI1024X-T1-E3 | ➔ SI1024X-T1-GE3 |
| ⊣ SI1024X-T1-GE3 | ⊛ SI1024X-T1-GE3 | ↔ SI1025X-T1 | ➔ SI1025X-T1-E3 | ➔ SI1025X-T1-E3 |
| ⊛ SI1026X-T1 | ⊣ SI1026X-T1-E3 | ⊛ SI1026X-T1-E3 | D SI1026X-T1-GE3 | ➔ SI1026X-T1-GE3 |
| ↔ SI1028X-T1-GE3 | ⊛ SI1028X-T1-GE3 | ⊣ SI1029X-T1-GE3 | ⊛ SI1029X-T1-GE3 | ➔ SI1031R-T1 |

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